

1. Material Substrate GaAs (N Type)
Epitaxial Layer GaAs (P/N Type)

2. Electrode N(Cathode) Side Gold Alloy
P(Anode) Side Aluminum Alloy

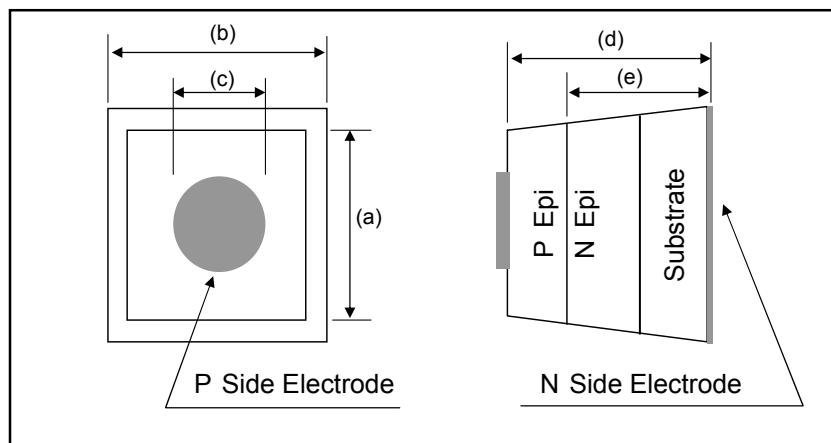
3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	V_F		1.3	1.45	V	IF=20mA
Reverse Voltage	V_R	8			V	IR=10uA
Power	P_O	A	1.14		mW	IF=20mA
		B	1.22			
		C	1.30			
		D	1.38			
		E	1.46			
		F	1.54			
Wavelength	λ_P		940		nm	IF=20mA
	$\Delta\lambda$		45		nm	IF=20mA

※ Note : LED Chip is mounted on TO-18 gold header without resin coating

4. Mechanical Data

- (a) Emission Area ----- 9mil x 9mil
- (b) Bottom Area ----- 10mil x 10mil
- (c) Bonding Pad ----- 130um
- (d) Chip Thickness ----- 10mil
- (e) Junction Height ----- 6.5mil



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